

Title (en)

METHOD FOR MANUFACTURING A CRYSTALLINE LAYER OF PZT MATERIAL, AND SUBSTRATE FOR EPITAXIALLY GROWING A CRYSTALLINE LAYER OF PZT MATERIAL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER KRISTALLINEN SCHICHT AUS PZT-MATERIAL UND SUBSTRAT ZUM EPITAKTISCHEN WACHSEN EINER KRISTALLINEN SCHICHT AUS PZT-MATERIAL

Title (fr)

PROCEDE DE FABRICATION D'UNE COUCHE CRISTALLINE DE MATERIAU PZT ET SUBSTRAT POUR CROISSANCE PAR EPITAXIE D'UNE COUCHE CRISTALLINE DE MATERIAU PZT

Publication

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Application

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Priority

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- IB 2019000201 W 20190326

Abstract (en)

[origin: WO2019186264A1] Method for manufacturing a crystalline layer of PZT material, including transferring a monocrystalline seed layer of SrTiO3 material onto a support substrate of silicon material, followed by epitaxially growing the crystalline layer of PZT material.

IPC 8 full level

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CPC (source: EP KR US)

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